## **Amendments to the Claims**

Please amend the claims as shown below. This **Listing of Claims** will replace all prior versions, and listings, of claims in the application.

- 1-11. (Cancelled)
- 12. (Currently amended) A method for manufacturing a test sensor, comprising:

forming a multiple layer device, including depositing a first metallic layer onto a substrate material by physical vapor deposition; depositing an intermediate, sacrificial layer on said metallic layer; and depositing an electrically non-conductive layer adjacent said intermediate, sacrificial layer by plasma enhanced chemical vapor deposition; and

applying an amount of energy to said multiple layer device an amount of energy ineffective to ablate said electrically non-conductive layer directly, but effective to selectively remove ablate a portion of said intermediate, sacrificial layer, thereby removing said intermediate, sacrificial layer and causing a corresponding portion of either said metallic layer or said non-conductive layer to be removed.

- 13. (Cancelled)
- 14. (Previously Presented) The method of claim 12, wherein said amount of energy is in the range of approximately 40 mJ/cm<sup>2</sup> to 450 mJ/cm<sup>2</sup>.
- 15. (Previously Presented) The method of claim 12, wherein said energy is provided by an ion-beam.
- 16. (Previously Presented) The method of claim 12, wherein said energy is provided by an electron beam.

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- 17. (Previously Presented) The method of claim 12, wherein the metallic layer includes at least one of copper, silver, gold, platinum, palladium, nickel, or aluminum.
- 18. (Previously Presented) The method of claim 12, wherein the electrically non-conductive layer has a thickness less than or substantially equal to  $1 \mu m$ .
- 19. (Previously Presented) The method of claim 12, wherein the intermediate, sacrificial layer is made of polytetrafluorethylene.
- 20. (Previously Presented) The method of claim 19, wherein the intermediate, sacrificial layer is deposited onto said metallic layer by plasma enhanced chemical vapor deposition.
- 21. (Previously Presented) The method of claim 12, wherein the substrate is made of a polymer material.
  - 22. (Previously presented) The method of claim 21, wherein the substrate is flexible.
  - 23. (Currently amended) The method of claim 12, further comprising:

depositing at least one of a second metallic layer, and a second intermediate, sacrificial layer, or a second non-metallic conductive layer on said multiple layer device and removing said second metallic layer by ablating an intermediate, sacrificial layer.

- 24. (Cancelled)
- 25. (Previously Presented) The method of claim 12, further comprising:

performing plasma activation before depositing said metallic layer, said non-conductive layer, or said intermediate layer.

- 26. (Previously Presented) The method of claim 12, wherein said energy is provided by a laser.
- 27. (Currently amended) The method of claim 12, wherein the intermediate, sacrificial layer is made of a Teflon-like compound of the formula C<sub>x</sub>F<sub>y</sub>.
- 28. (Previously Presented) The method of claim 12, wherein the electrically non-conductive layer is made of a ceramic layer comprising MgO.
- 29. (Currently amended) The method of claim 12, wherein the electrically non-conductive layer is not suitable for laser ablation comprises one or more members of the group consisting of MgO, SiO, and MgF<sub>2</sub>.